

The listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1.-38. (Canceled)

39. (Previously Presented) A display device comprising:

a pair of resinous substrates facing each other and having an uneven surface;
a resinous layer formed on at least one of the pair of resinous substrates, wherein the resinous layer planarizes the uneven surface;
a thin film transistor formed over the resinous layer;
a layer comprising a resinous material covering the thin film transistor; and
a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

40. (Previously Presented) A display device comprising:

a pair of flexible substrates facing each other and having an uneven surface;
a resinous layer formed on at least one of the pair of flexible substrates, wherein the resinous layer planarizes the uneven surface;
a thin film transistor formed over the resinous layer;
a layer comprising a resinous material covering the thin film transistor; and
a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

41. (Previously Presented) A display device comprising:

a pair of resinous substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of resinous substrates, wherein the resinous layer planarizes the uneven surface;
a thin film transistor formed over the resinous layer;
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and
a pixel electrode formed over the silicon oxide film, and electrically connected to the thin film transistor.

42. (Previously Presented) A display device comprising:
a pair of flexible substrates facing each other and having an uneven surface;
a resinous layer formed on at least one of the pair of flexible substrates, wherein the resinous layer planarizes the uneven surface;
a thin film transistor formed over the resinous layer;
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and
a pixel electrode formed over the silicon oxide film, and electrically connected to the thin film transistor.

43. (Previously Presented) A display device comprising:
a pair of resinous substrates facing each other and having an uneven surface;
a resinous layer formed on at least one of the pair of resinous substrates, wherein the resinous layer planarizes the uneven surface;
a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising amorphous silicon;
a layer comprising a resinous material covering the thin film transistor; and
a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

44. (Previously Presented) A display device comprising:

a pair of flexible substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of flexible substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising amorphous silicon;

a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

45. (Previously Presented) A display device comprising:

a pair of resinous substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of resinous substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising amorphous silicon;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the silicon oxide film, and electrically connected to the thin film transistor.

46. (Previously Presented) A display device comprising:

a pair of flexible substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of flexible substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising amorphous silicon;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the silicon oxide film, and electrically connected to the thin film transistor.

47. (Previously Presented) A display device comprising:

a pair of resinous substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of resinous substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising microcrystalline silicon;

a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

48. (Previously Presented) A display device comprising:

a pair of flexible substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of flexible substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising microcrystalline silicon;

a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

49. (Previously Presented) A display device comprising:

a pair of resinous substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of resinous substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising microcrystalline silicon;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the silicon oxide film, and electrically connected to the thin film transistor.

50. (Previously Presented) A display device comprising:

a pair of flexible substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of flexible substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising microcrystalline silicon;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the silicon oxide film, and electrically connected to the thin film transistor.

51. (Previously Presented) A display device comprising:

a pair of resinous substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of resinous substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising crystalline silicon;

a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

52. (Previously Presented) A display device comprising:
a pair of flexible substrates facing each other and having an uneven surface;
a resinous layer formed on at least one of the pair of flexible substrates, wherein the resinous layer planarizes the uneven surface;
a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising crystalline silicon;
a layer comprising a resinous material covering the thin film transistor; and
a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

53. (Previously Presented) A display device comprising:
a pair of resinous substrates facing each other and having an uneven surface;
a resinous layer formed on at least one of the pair of resinous substrates, wherein the resinous layer planarizes the uneven surface;
a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising crystalline silicon;
a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and
a pixel electrode formed over the silicon oxide film, and electrically connected to the thin film transistor.

54. (Previously Presented) A display device comprising:
a pair of flexible substrates facing each other and having an uneven surface;
a resinous layer formed on at least one of the pair of flexible substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising crystalline silicon;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the silicon oxide film, and electrically connected to the thin film transistor.

55. (Previously Presented) A display device comprising:

a pair of resinous substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of resinous substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising crystalline silicon formed by irradiating an amorphous silicon film with a laser light;

a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

56. (Previously Presented) A display device comprising:

a pair of flexible substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of flexible substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising crystalline silicon formed by irradiating an amorphous silicon film with a laser light;

a layer comprising a resinous material covering the thin film transistor; and

a pixel electrode formed over the layer, and electrically connected to the thin film transistor.

57. (Previously Presented) A display device comprising:

a pair of resinous substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of resinous substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising crystalline silicon formed by irradiating an amorphous silicon film with a laser light;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the silicon oxide film, and electrically connected to the thin film transistor.

58. (Previously Presented) A display device comprising:

a pair of flexible substrates facing each other and having an uneven surface;

a resinous layer formed on at least one of the pair of flexible substrates, wherein the resinous layer planarizes the uneven surface;

a thin film transistor formed over the resinous layer, wherein the thin film transistor has a channel formation region comprising crystalline silicon formed by irradiating an amorphous silicon film with a laser light;

a silicon oxide film covering the thin film transistor, wherein the silicon oxide film is formed by applying a liquid; and

a pixel electrode formed over the silicon oxide film, and electrically connected to the thin film transistor.

59. (Previously Presented) A display device according to any one of claims 55-58, wherein the laser light comprises at least one selected from the group consisting of KrF excimer laser light and XeCl laser light.

60. (Previously Presented) A display device according to any one of claims 39-58, wherein the resinous layer comprises an acrylic resin.

61. (Previously Presented) A display device according to any one of claims 39-58, wherein the resinous layer comprises at least one selected from the group consisting of methyl esters of acrylic acid, ethyl esters of acrylic acid, butyl esters of acrylic acid, and 2-ethylhexyl esters of acrylic acid.

62.-65. (Canceled)

66. (Currently Amended) A display device according to any one of claims ~~35-58~~ 39-58, wherein the thin film transistor comprises a coplanar thin-film transistor.

67. (Currently Amended) A display device according to any one of claims ~~35-58~~ 39-58, wherein the thin film transistor comprises an inverted-staggered thin-film transistor.

68. (Currently Amended) A display device according to any one of claims ~~35, 37, 39, 41, 43, 45, 47, 49, 51, 53, 55 and 57~~, wherein the pair of resinous substrates comprise at least one selected from the group consisting of PET (polyethylene terephthalate), PEN (polyethylene naphthalate), PES (polyethylene sulfite), and polyimide.

69. (Currently Amended) A display device according to any one of claims ~~36, 38, 40, 42, 44, 46, 48, 50, 52, 54, 56 and 58~~, wherein the pair of flexible substrates comprise at least one selected from the group consisting of PET (polyethylene

terephthalate), PEN (polyethylene naphthalate), PES (polyethylene sulfite), and polyimide.